

# PJE138K

## 50V N-Channel Enhancement Mode MOSFET – ESD Protected

**Voltage**

**50 V**

**Current**

**350mA**

### Features

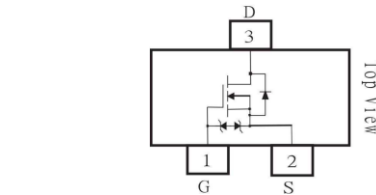
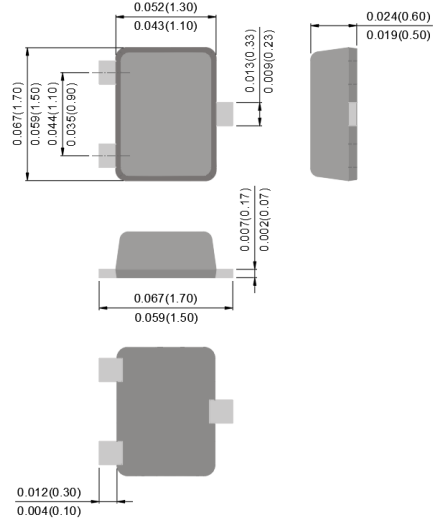
- RDS(ON) , VGS@10V, ID@500mA<1.6Ω
- RDS(ON) , VGS@4.5V, ID@200mA<2.5Ω
- RDS(ON) , VGS@2.5V, ID@100mA<4.5Ω
- Advanced Trench Process Technology
- Specially Designed for Battery Operated Systems, Solid-State Relays Drivers: Relay, Displays, Memories, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### Mechanical Data

- Case : SOT-523 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.002 grams

SOT-523

Unit : inch(mm)



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V <sub>DS</sub>	50	V
Gate-Source Voltage	V <sub>GS</sub>	+20	V
Continuous Drain Current	I <sub>D</sub>	350	mA
Pulsed Drain Current	I <sub>DM</sub>	1200	mA
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	223
		Derate above 25°C	1.8
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55~150	°C
Typical Thermal Resistance	R <sub>θJA</sub>	560	°C/W
- Junction to Ambient <sup>(Note 3)</sup>			

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## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	50	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.8	1.0	1.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =500mA	-	0.96	1.6	Ω
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =200mA	-	1.25	2.5	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =100mA	-	2.73	4.5	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V	-	0.01	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	±3.0	±10	uA
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =25V, I <sub>D</sub> =250mA, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	0.63	1	nC
Gate-Source Charge	Q <sub>gs</sub>		-	0.2	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	0.23	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	25	50	pF
Output Capacitance	C <sub>oss</sub>		-	9.5	20	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	2.1	5	
<b>Switching</b>						
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =25V, I <sub>D</sub> =500mA, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω <sup>(Note 1,2)</sup>	-	2.2	5	ns
Turn-On Rise Time	t <sub>r</sub>		-	19.2	38	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	6.2	12	
Turn-Off Fall Time	t <sub>f</sub>		-	23	50	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>	---	-	-	500	mA
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =500mA, V <sub>GS</sub> =0V	-	0.86	1.5	V

NOTES:

1. Pulse width ≤ 300us, Duty cycle ≤ 2%
2. Essentially independent of operating temperature typical characteristics.
3. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. mounted on a 1 inch square pad of copper

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## TYPICAL CHARACTERISTIC CURVES

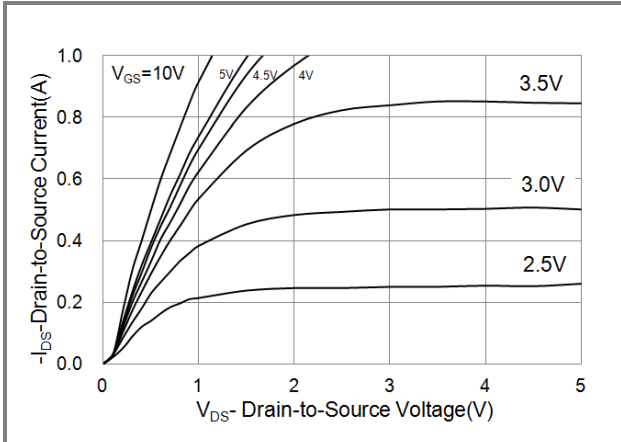


Fig.1 On-Region Characteristics

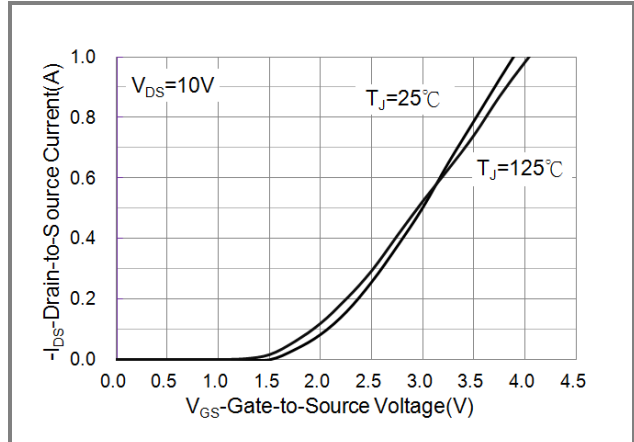


Fig.2 Transfer Characteristics

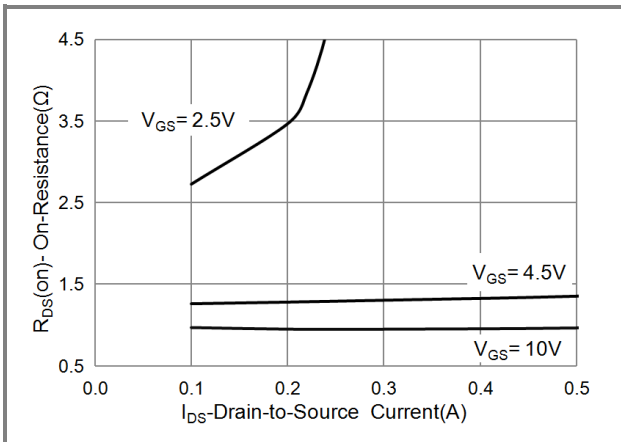


Fig.3 On-Resistance vs. Drain Current

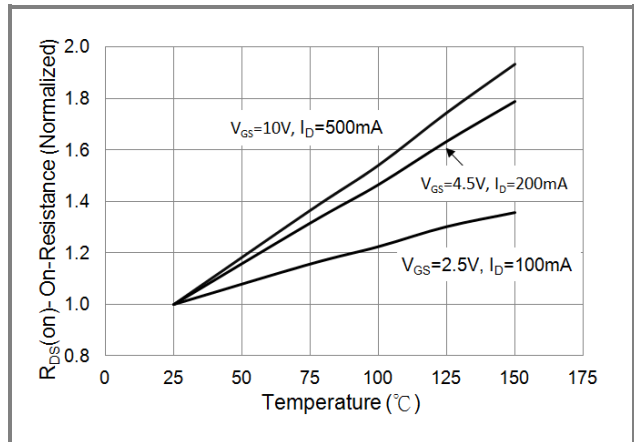


Fig.4 On-Resistance vs. Junction temperature

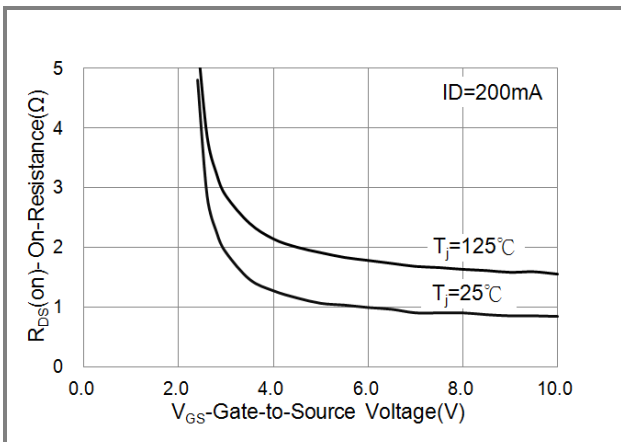


Fig.5 On-Resistance Variation with V\_GS.

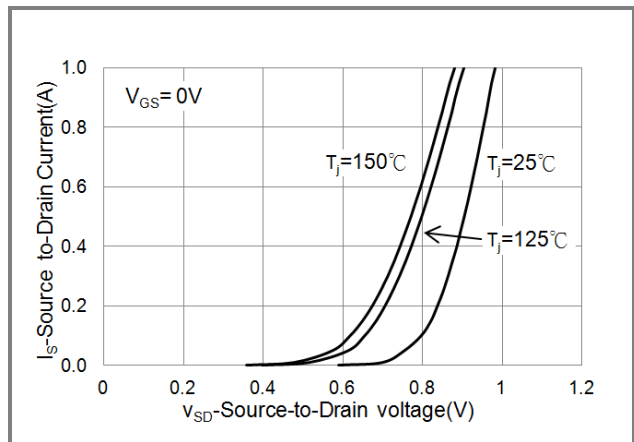
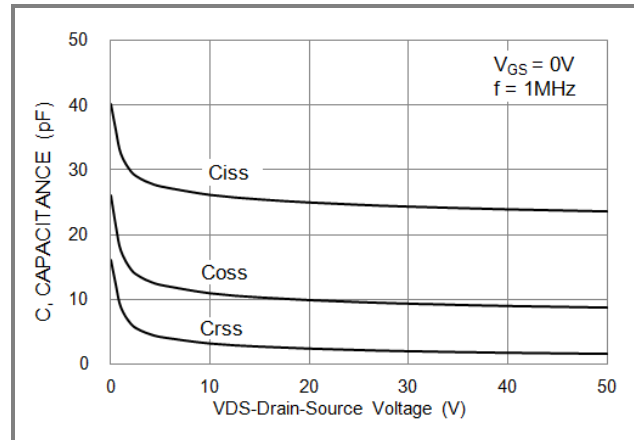
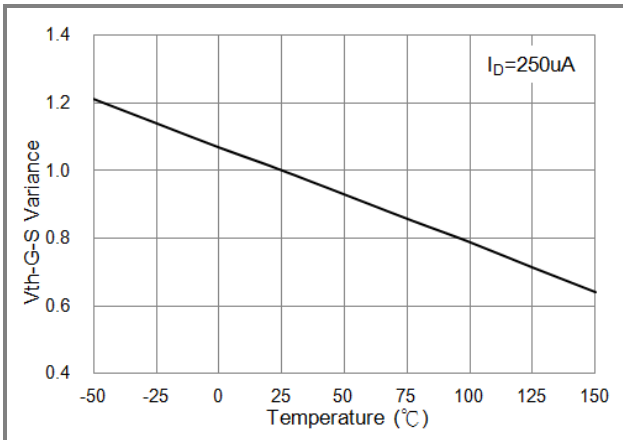
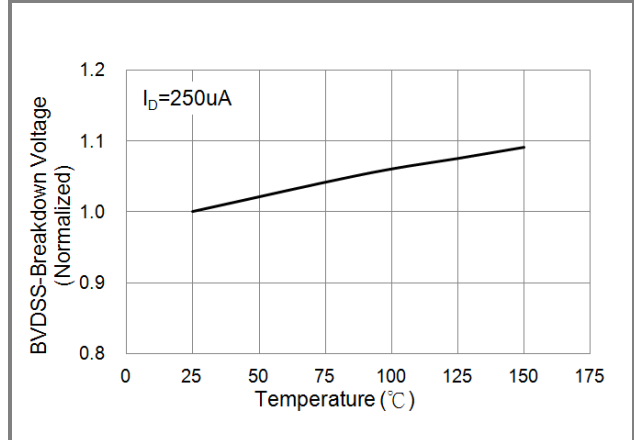
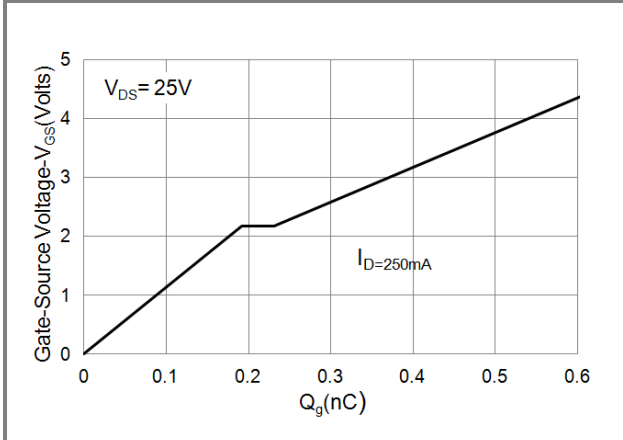


Fig.6 Body Diode Characteristics

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## TYPICAL CHARACTERISTIC CURVES

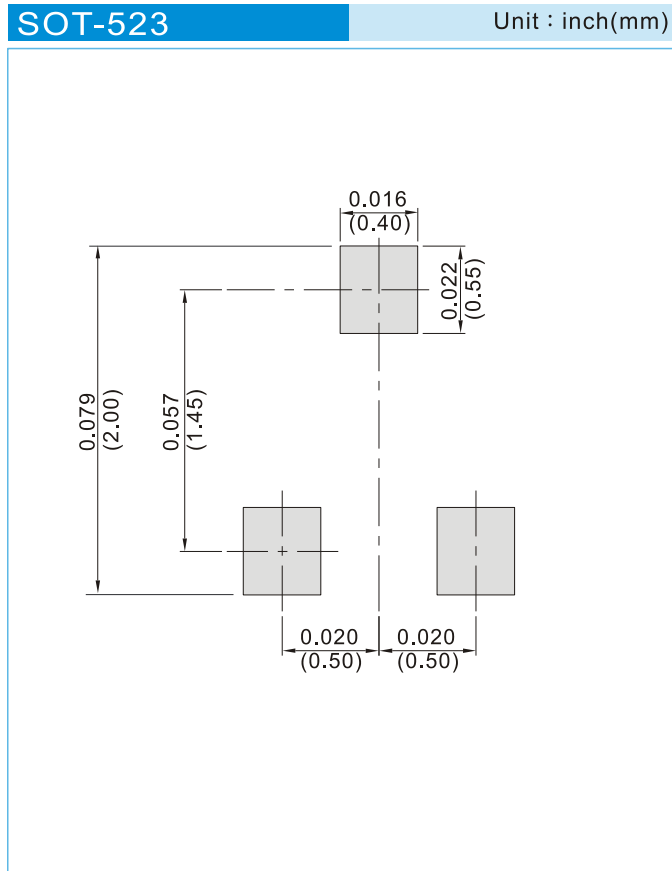


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## Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJE138K	SOT-523	4K pcs / 7" reel	8KT

## Mounting Pad Layout



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